## MEMORY

CMOS
MASK ROM CARD
PCMCIA Rel.2/JEIDA Ver. 4 conformable

## MB98A51121/51221/51321/51421/51521-17

## MASK ROM CARD 2 M/4 M/8 M/16 M/32 M-BYTE

## ■ DESCRIPTION

This card is a PCMCIA and JEIDA-compliant 68-pin two-piece Mask ROM card with the 16-bit mask ROM being installed on the common memory.
However, to use this card as PCMCIA Rel.2, JEIDA Ver.4, the card attribute information has to be stored in the Mask ROM.

## ■ FEATURES

- External dimensions: $85.6 \mathrm{~mm} \times 54.0 \mathrm{~mm} \times 3.3 \mathrm{~mm}$
- +5 V single power supply
- Usable in 8 bits $\times 16$ bits configuration
- Complete static operation
- I/O level TTL compatible
- Output tri-state
- Complete capacitive load without pull-up resistor or pull-down resistor except $\overline{\mathrm{CE}}_{1}$ and $\overline{\mathrm{CE}}_{2}$.
-68-pin two-piece connector form


## PACKAGE


(CRD-68P-M04)

## PRODUCT CLASS

| Part Number | Memory Device | Memory Configuration <br> (word $\times$ bit) | Access Time (ns) (max.) |
| :--- | :--- | :---: | :---: |
| MB98A51121 | 16-Mbit Mask ROM $\times 1 \mathrm{pcs}$ | $2 \mathrm{M} \times 8 / 1 \mathrm{M} \times 16$ |  |
| MB98A51221 | 16-Mbit Mask ROM $\times 2 \mathrm{pcs}$ | $4 \mathrm{M} \times 8 / 2 \mathrm{M} \times 16$ | 170 |
| MB98A51321 | 16-Mbit Mask ROM $\times 4 \mathrm{pcs}$ | $8 \mathrm{M} \times 8 / 4 \mathrm{M} \times 16$ |  |
| MB98A51421 | 16-Mbit Mask ROM $\times 8 \mathrm{pcs}$ | $16 \mathrm{M} \times 8 / 8 \mathrm{M} \times 16$ |  |
| MB98A51521 | 16-Mbit Mask ROM $\times 16 \mathrm{pcs}$ | $32 \mathrm{M} \times 8 / 16 \mathrm{M} \times 16$ |  |

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## PIN ASSIGNMENTS

(CONNECTOR SIDE)


- Pin Name

| Symbol | I/O | Pin Name |
| :---: | :---: | :---: |
| A 0 to $\mathrm{A}_{25}$ | 1 | Address input |
| D ${ }_{0}$ to $\mathrm{D}_{15}$ | I/O | Data I/O |
| $\overline{C E}_{1}, \overline{C E}_{2}$ | 1 | Card enable |
| $\overline{\mathrm{CD}}_{1}, \overline{\mathrm{CD}}_{2}$ * | O | Card detection |
| $\overline{\mathrm{VS}} 1_{1}, \mathrm{VS}_{2}$ | O | Voltage sense |
| REG | I | Attribute memory space select |
| $\overline{\mathrm{OE}}$ | 1 | Output enable |
| $\overline{W E}$ | 1 | Write enable |
| BVD1, BVD2 * | O | Battery voltage detection |
| WP * | O | Write protect |
| Vcc | - | Supply voltage (+5 V) |
| GND | - | Ground |
| N.C. | - | No connection |

*: Those pins are internally connected; use care when handling.

| Pin No. | Symbol | Pin No. | Symbol |
| :---: | :---: | :---: | :---: |
| 1 | GND | 35 | GND |
| 2 | $\mathrm{D}_{3}$ | 36 | $\overline{C D}_{1}$ |
| 3 | D4 | 37 | D11 |
| 4 | D5 | 38 | $\mathrm{D}_{12}$ |
| 5 | D6 | 39 | $\mathrm{D}_{13}$ |
| 6 | D7 | 40 | D14 |
| 7 | $\overline{\mathrm{CE}}_{1}$ | 41 | $\mathrm{D}_{15}$ |
| 8 | $\mathrm{A}_{10}$ | 42 | $\overline{\mathrm{CE}} 2$ |
| 9 | $\overline{\mathrm{OE}}$ | 43 | $\overline{\mathrm{VS}}_{1}$ * |
| 10 | $\mathrm{A}_{11}$ | 44 | N.C. |
| 11 | A9 | 45 | N.C. |
| 12 | $\mathrm{A}_{8}$ | 46 | $\mathrm{A}_{17}$ |
| 13 | $\mathrm{A}_{13}$ | 47 | $\mathrm{A}_{18}$ |
| 14 | $\mathrm{A}_{14}$ | 48 | $\mathrm{A}_{19}$ * |
| 15 | WE/N.C. * | 49 | $\mathrm{A}_{20}$ * |
| 16 | N.C. | 50 | $\mathrm{A}_{21} / \mathrm{N} . \mathrm{C}$. * |
| 17 | Vcc | 51 | Vcc |
| 18 | N.C. | 52 | N.C. |
| 19 | $\mathrm{A}_{16}$ | 53 | A22/N.C. * |
| 20 | $\mathrm{A}_{15}$ | 54 | $\mathrm{A}_{23} /$ N.C. * |
| 21 | $\mathrm{A}_{12}$ | 55 | A24/N.C. * |
| 22 | $\mathrm{A}_{7}$ | 56 | A25/N.C. * |
| 23 | $\mathrm{A}_{6}$ | 57 | $\overline{\mathrm{VS}}_{2}$ * |
| 24 | $\mathrm{A}_{5}$ | 58 | N.C. |
| 25 | $\mathrm{A}_{4}$ | 59 | N.C. |
| 26 | $\mathrm{A}_{3}$ | 60 | N.C. |
| 27 | $\mathrm{A}_{2}$ | 61 | $\overline{\mathrm{REG}} / \mathrm{N} . \mathrm{C} . *$ |
| 28 | $\mathrm{A}_{1}$ | 62 | BVD2 |
| 29 | $A_{0}$ | 63 | BVD1 |
| 30 | $\mathrm{D}_{0}$ | 64 | D8 |
| 31 | D1 | 65 | D9 |
| 32 | $\mathrm{D}_{2}$ | 66 | $\mathrm{D}_{10}$ |
| 33 | WP | 67 | $\overline{C D}_{2}$ |
| 34 | GND | 68 | GND |

*: Whether a pin is an address pin or N.C. pin depends on the type of the models. See $\square$ DIFFERENCE OF PIN FUNCTIONS.

DIFFERENCE OF PIN FUNCTIONS

| Part Name | A 21 | $\mathrm{A}_{22}$ | $\mathrm{A}_{23}$ | $\mathrm{A}_{24}$ | $\mathrm{A}_{25}$ | REG | WE | $\overline{V S}_{1}$ | $\mathrm{VS}_{2}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| MB98A51121 | N.C. | N.C. | N.C. | N.C. | N.C. | N.C. | N.C. | N.C. | N.C. |
| MB98A51221 | $\mathrm{A}_{21}$ |  |  |  |  |  |  |  |  |
| MB98A51321 |  | $\mathrm{A}_{22}$ |  |  |  |  |  |  |  |
| MB98A51421 |  |  |  |  |  |  |  |  |  |
| MB98A51521 |  |  | $\mathrm{A}_{23}$ | $\mathrm{A}_{24}$ |  |  |  |  |  |

## BLOCK DIAGRAM

## 1. 16-Mbit Mask ROM $\times 1 / \times 2 / \times 4$ Being Mounted



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## 2. 16-Mbit Mask ROM $\times 8 / \times 16$


*1, *2: Varies with the type of models.

| Part Number | $\mathrm{A}_{22}$ | $\mathrm{~A}_{23}$ | $\mathrm{~A}_{24}$ | M0/1 | M2/3 | M4/5 | M6/7 | M8/9 | M10/11 | M12/13 | M14/15 |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| MB98A51421 | $\mathrm{A}_{22}$ | $\mathrm{~A}_{23}$ | $\mathrm{~N} . \mathrm{C}$. | $\mathrm{M} 0 / 1$ | $\mathrm{M} 2 / 3$ | $\mathrm{M} 4 / 5$ | $\mathrm{M} 6 / 7$ | - | - | - | - |
| MB98A51521 | $\mathrm{A}_{22}$ | $\mathrm{~A}_{23}$ | $\mathrm{~A}_{24}$ | $\mathrm{M} 0 / 1$ | $\mathrm{M} 2 / 3$ | $\mathrm{M} 4 / 5$ | $\mathrm{M} 6 / 7$ | $\mathrm{M} 8 / 9$ | $\mathrm{M} 10 / 11$ | $\mathrm{M} 12 / 13$ | $\mathrm{M} 14 / 15$ |

## FUNCTIONAL TRUTH TABLE

| $\overline{\mathbf{C E}}_{2}$ | $\overline{\mathbf{C E}}_{\mathbf{1}}$ | $\mathbf{A}_{0}$ <br> (BYTE) | $\overline{\mathbf{O E}}$ | Operating Mode | Output Pin <br> $\left(\mathrm{D}_{8}\right.$ to $\left.\mathrm{D}_{15}\right)$ | Output Pin <br> (Do to $\left.\mathrm{D}_{7}\right)$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| H | H | $\times$ | $\times$ | Standby | High-impedance | High-impedance |
| $\times$ | $\times$ | $\times$ | H | Output disable | High-impedance | High-impedance |
| H | L | L | L | Read $(\times 8$ bit) | High-impedance | Output data <br> (even bytes) |
| H | L | H | L | Read $(\times 8$ bit) | High-impedance | Output data <br> (odd bytes) |
| L | H | $\times$ | L | Read $(\times 8$ bit) | Output data <br> (odd bytes) | High-impedance |
| L | L | $\times$ | L | Read $(\times 16$ bit) | Output data <br> (odd bytes) | Output data <br> (even bytes) |

H: High level, L: Low level, $\times$ : Don't care

## ABSOLUTE MAXIMUM RATINGS (See WARNING)

| Parameter | Symbol | Value |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Max. | Min. |  |
| Supply Voltage * | Vcc | -0.3 | +6.0 | V |
| Input Voltage * | Vin | -0.3 | $\mathrm{Vcc}+0.3$ | V |
| Output Voltage * | Vout | -0.3 | V cc +0.3 | V |
| Ambient Temperature | $\mathrm{T}_{\mathrm{A}}$ | -10 | +60 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | $\mathrm{T}_{\text {stg }}$ | -30 | +70 | ${ }^{\circ} \mathrm{C}$ |

* : The voltage values are with reference to GND $=0 \mathrm{~V}$.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

## RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | Value |  |  | Unit |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typ. | Max. |  |
| Supply Voltage * | V cc | 4.75 | 5.0 | 5.25 | V |
|  | GND | - | 0 | - | V |
| Low Level Input Voltage $^{*}$ | $\mathrm{~V}_{\mathrm{IH}}$ | 2.4 | - | $\mathrm{V}_{\mathrm{CC}}+0.3$ | V |
| Ambient Temperature | $\mathrm{V}_{\mathrm{IL}}$ | -0.3 | - | 0.8 | V |

[^0]WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.
Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.
No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

## ELECTRICAL CHARACTERISTICS

## 1. DC Characteristics

(On the recommended conditions)

| Parameter | Notes | Symbol | Test Conditions | Value |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min. | Typ. | Max. |  |
| Standby Supply Current |  | Isb1 | $\begin{aligned} & \overline{\mathrm{CE}}_{1}, \overline{\mathrm{CE}}_{2} \geqq \mathrm{~V}_{\mathrm{cc}}-0.2 \mathrm{~V} \\ & \text { lout }=0 \mathrm{~mA} \end{aligned}$ | - | 10 | 1600 | $\mu \mathrm{A}$ |
|  |  | Isb2 | $\begin{aligned} & \overline{\mathrm{CE}}_{1}, \overline{\mathrm{CE}}_{2}=\mathrm{V}_{\mathrm{H}} \\ & \text { lout }=0 \mathrm{~mA} \end{aligned}$ | - | - | 10 | mA |
| Averaging Operation Supply Current |  | Icc | $\begin{aligned} & \text { Cycle }=\text { min. } \\ & \text { Duty cycle }=100 \% \\ & \text { lout }=0 \mathrm{~mA}, \overline{O E}=\mathrm{V}_{\mathrm{H}} \\ & \mathrm{~V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{H}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{aligned}$ | - | - | 220 | mA |
| Input Leak Current | *1 | IL | $\mathrm{V}_{\mathrm{I}}=0 \mathrm{~V}$ to $\mathrm{V}_{\mathrm{cc}}$ | -40 | $\pm 0.1$ | 40 | $\mu \mathrm{A}$ |
| Output Leak Current | *2 | ILo | Vout $=0 \mathrm{~V}$ to V cc , $\overline{\mathrm{CE}}_{1}, \overline{\mathrm{CE}}_{2}=\mathrm{V}_{\mathrm{IH}}$ or $\overline{\mathrm{OE}}=\mathrm{V}_{\mathrm{H}}$ | -10 | - | 10 | $\mu \mathrm{A}$ |
| High Level Output Voltage | *2 | Vон | $\mathrm{I} \mathrm{O}=-1 \mathrm{~mA}$ | 2.4 | - | - | V |
| Low Level Output Voltage | *2 | VoL | $\mathrm{loL}=2.1 \mathrm{~mA}$ | - | - | 0.4 | V |

Notes: *1. Excluding $\overline{\mathrm{CE}}_{1}$ and $\overline{\mathrm{CE}}_{2}$ pins.
${ }^{*}$ 2. Excluding WP, BVD1, BVD2, $\overline{C D}_{1}$ and $\overline{C D}_{2}$ pins.

## 2. AC Characteristics

(1) Common Memory read cycle
(On the recommended conditions)

| Parameter | Notes | Symbol | Test Conditions | Value |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min. | Max. |  |
| Read Cycle Time |  | trc | - | 170 | - | ns |
| Address Cycle Time |  | tacc | $\begin{aligned} & \overline{\mathrm{CE}}=\mathrm{V}_{\mathrm{H}}, \mathrm{~V}_{\mathrm{IL}} \\ & \overline{\mathrm{OE}}=\mathrm{V}_{\mathrm{IL}} \end{aligned}$ | - | 170 | ns |
| Card Enable Access Time |  | tce | $\overline{\mathrm{OE}}=\mathrm{V}_{\text {IL }}$ | - | 170 | ns |
| Output Enable Access Time | *1 | toe | $\overline{\mathrm{CEx}}=\mathrm{V}_{\text {IH }}, \mathrm{V}_{\mathrm{IL}}$ | - | 75 | ns |
| Output Disable Time | *2 | tof | - | - | 60 | ns |
| Output Hold Time |  | tон | $\begin{aligned} & \overline{\mathrm{CE}} \mathrm{x}=\mathrm{V}_{\mathrm{H}}, \mathrm{~V}_{\mathrm{IL}} \\ & \overline{\mathrm{OE}}=\mathrm{V}_{\mathrm{IL}} \end{aligned}$ | 0 | - | ns |

Notes: *1. The maximum delay of $\overline{O E}$ is $t_{A C C}$ - toE within the ranges in which the $t_{A C c}$ is not affected.
*2. tDF is determined by either $\overline{\mathrm{CE}}$ or $\overline{\mathrm{OE}}$, whichever is faster with rise time.
The decision level is determined by the time the output is in a high-impedance state.
3. Input/output Terminal Capacitance

| Parameter | Notes | Symbol | $\left(\mathrm{Vin}^{\prime}, \mathrm{V}_{\text {out }}=\mathrm{GND}, \mathrm{f}=1 \mathrm{MHz}, \mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}\right)$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Value |  | Unit |
|  |  |  | Min. | Max. |  |
| Input Terminal Capacitance | *1 | Cin | - | 75 | pF |
| Output Terminal Capacitance | *2 | Cıo | - | 50 | pF |

Notes: *1. Excluding $\overline{\mathrm{CE}}_{1}$ and $\overline{\mathrm{CE}}_{2}$ pins.
*2. Excluding WP, BVD1, BVD2, $\overline{C D}_{1}$, and $\overline{C D}_{2}$ pins.
4. AC Characteristics Test Conditions

Input voltage
Input pulse rise time, fall time
Timing measurement reference voltage

Output load

$$
\text { : Input } \quad: \mathrm{V}_{H}=2.4 \mathrm{~V}
$$

$$
\begin{aligned}
& : \mathrm{V}_{\mathrm{IH}}=2.6 \mathrm{~V}, \mathrm{~V}_{\mathrm{IL}}=0.6 \mathrm{~V} \\
& : \mathrm{tr}, \mathrm{tf}=5 \mathrm{~ns}(0.8 \mathrm{~V} \text { to } 2.4 \mathrm{~V}) \\
& : \mathrm{V}_{\mathrm{H}}=2.4 \mathrm{~V} \\
& : \mathrm{V}_{\mathrm{IL}}=0.8 \mathrm{~V} \\
& : \mathrm{VoH}^{2}=2.2 \mathrm{~V} \\
& : \mathrm{VoL}^{2}=0.8 \mathrm{~V} \\
& : 1 \mathrm{TTL}+\mathrm{CL}_{\mathrm{L}}(100 \mathrm{pF})
\end{aligned}
$$

- Output load circuit



## TIMING DIAGRAM

## 1. Common Memory Read Cycle


(Continued)
(Continued)

*: tDF is determined by either $\overline{\mathrm{OE}}$ or $\overline{\mathrm{CE}}_{1}=\overline{\mathrm{CE}}_{2}$, whichever is faster with rise time.
The decision level is determined by the time the output is in a high-impedance state.

## DATA RELEASE METHOD

Data release is accepted by the 8 -Mbit EPROM ( 1 Mword $\times 8$ bits).
To prevent erroneous writing of data, provide three samples per piece of data. Also indicate the card memory address for writing.

- Mapping between release data EPROM address and memory card address ( 16 Mbit Mask ROM $\times 1 / \times 2 / \times 4$ being mounted)
The range of the address for the MB98A51121 is 000000 to 1FFFFF ( 2 Mbytes).
The range of the address for the MB98A51221 is 000000 to 3FFFFF ( 4 Mbytes).
The range of the address for the MB98A51321 is 000000 to 7FFFFF ( 8 Mbytes).

- Mapping between release data EPROM address and memory card address ( 16 Mbit Mask ROM $\times 8 / \times 16$ being mounted)

The range of the address for the MB98A51421 is 000000 to FFFFFF ( 16 Mbytes).
The range of the address for the MB98A51521 is 0000000 to1FFFFFF ( 32 Mbytes)

(Continued)


## MB98A51121/51221/51321/51421/51521-17

## AUXILIARY CAPABILITIES

## 1. Card Detection Pins ( $\overline{\mathrm{CD}}_{1}, \overline{\mathrm{CD}}_{2}$ )

These pins verify a card is correctly inserted into the system.
The two pins are internally connected to the ground; with the system side connection being pulled up to the Vcc , detection of the voltage of these pins allows the system to check the state of connectivity of a card (See the diagram below).

2. Write Protection Pin (WP)

The Mask ROM Card, whose common memory is write-protected, outputs a high-level write-protection signal.

## DEVICE HANDLING PRECAUTIONS

The device in composed of fine electronic parts, so take care in handling or keeping it as below.

- The card is made fine, so do not keep it in the high temperature nor high humiditly, place line in the direct sunshine nor near the heater.
- The card should not be bent, scratched, dropped nor be shocked violently.
- This device should never be taken a part. It could destroy the card or your personal computer hardware.
- To help you handle this device safely, request us the device specifications when purchasing this device.


## MB98A51121/51221/51321/51421/51521-17

## PACKAGE DIMENSIONS



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[^0]:    *: The voltage values are with reference to the GND $=0 \mathrm{~V}$.

